Features

- Split Gate Trench MOSFET Technology
- Excellent Package for Heat Dissipation
- High Density Cell Design for Low $R_{DS(ON)}$
- Halogen Free. “Green” Device (Note 1)
- Epoxy Meets UL 94 V-0 Flammability Rating
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)
- Moisture Sensitivity Level 1

N-CHANNEL MOSFET

Maximum Ratings

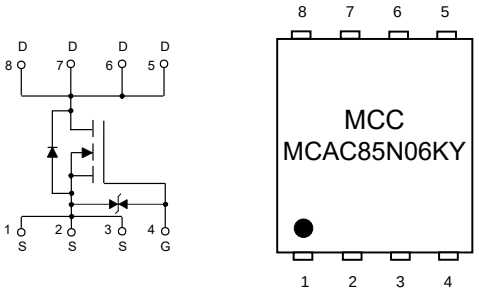
- Operating Junction Temperature Range : -55°C to +150°C
- Storage Temperature Range: -55°C to +150°C
- Thermal Resistance: 17°C/W Junction to Ambient(t≤10S)(2)
- Thermal Resistance: 55°C/W Junction to Ambient(Steady-State)(2)
- Thermal Resistance: 1.1°C/W Junction to Case(Steady-State)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Volltage	V_{GS}	±20	V
Continuous Drain Current	I_D	85	A
Pulsed Drain Current(3)	I_{DM}	340	A
Total Power Dissipation	P_D	110	W
Single Pulsed Avalanche Energy(4)	E_{AS}	400	mJ

Note:

1. Halogen free "Green” products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
2. The value of $R_{\theta JA}$ is measured with the device mounted on $1in^2$ FR-4 board with 2oz. Copper, in a still air environment with T_A =25°C. The Power dissipation P_{DSM} is based on $R_{\theta JA}$ t≤ 10s and the maximum allowed junction temperature of 150°C. The value in any given application depends on the user's specific board design.
3. Repetitive rating; pulse width limited by max. junction temperature.
4. T_J=25°C, V_{DD}=50V, L=2mH, I_{AS}=20A

Internal Structure and Marking Code



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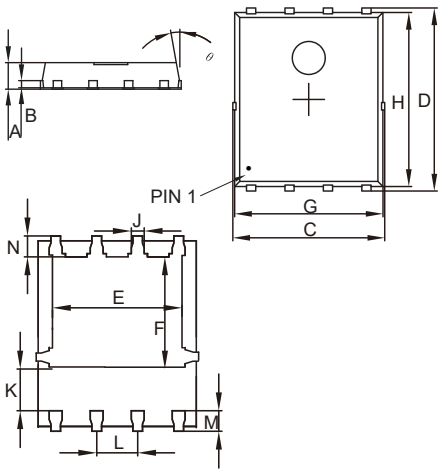


DIMENSIONS					
DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	0.031	0.047	0.80	1.20	
B	0.010		0.254		TYP.
C	0.193	0.222	4.90	5.64	
D	0.232	0.250	5.90	6.35	
E	0.148	0.167	3.75	4.25	
F	0.126	0.154	3.20	3.92	
G	0.189	0.213	4.80	5.40	
H	0.222	0.239	5.65	6.06	
K	0.045	0.059	1.15	1.50	
J	0.012	0.020	0.30	0.50	
L	0.046	0.054	1.17	1.37	
M	0.012	0.028	0.30	0.71	
N	0.016	0.028	0.40	0.71	

Electrical Characteristics @ 25°C (Unless Otherwise Specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS}=0V, I_D=250μA	60			V
Gate-Source Leakage Current	I_{GSS}	V_{DS}=0V, V_{GS} =±20V			±10	μA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=60V, V_{GS}=0V			1	μA
Gate-Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=250μA	1.0	1.6	2.5	V
Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS}=10V, I_D=20A		2.9	3.7	mΩ
		V_{GS}=4.5V, I_D=20A		3.8	5.0	mΩ
Gate Resistance	R_G	f=1MHz, Open drain		2		Ω
Diode Characteristics						
Continuous Body Diode Current	I_S				85	A
Diode Forward Voltage	V_{SD}	V_{GS}=0V, I_S=20A		0.8	1.3	V
Reverse Recovery Time	t_{rr}	I_F=20A, dI_F/dt=500A/μs		41.6		ns
Reverse Recovery Charge	Q_{rr}			39.8		nC
Dynamic Characteristics						
Input Capacitance	C_{iss}	V_{DS}=30V,V_{GS}=0V,f=1MHz		4650		pF
Output Capacitance	C_{oss}			850		
Reverse Transfer Capacitance	C_{rss}			65		
Total Gate Charge	Q_g	V_{DS}=30V,V_{GS}=10V,I_D=25A		70.78		nC
Gate-Source Charge	Q_{gs}			16.64		
Gate-Drain Charge	Q_{gd}			10.62		
Turn-On Delay Time	$t_{d(on)}$	V_{DS}=30V, V_{GEN}=10V, R_G=2Ω, I_{DS}=25A		15.9		ns
Turn-On Rise Time	t_r			55.2		
Turn-Off Delay Time	$t_{d(off)}$			57.5		
Turn-Off Fall Time	t_f			91.3		

Curve Characteristics

Fig. 1 - Typical Output Characteristics

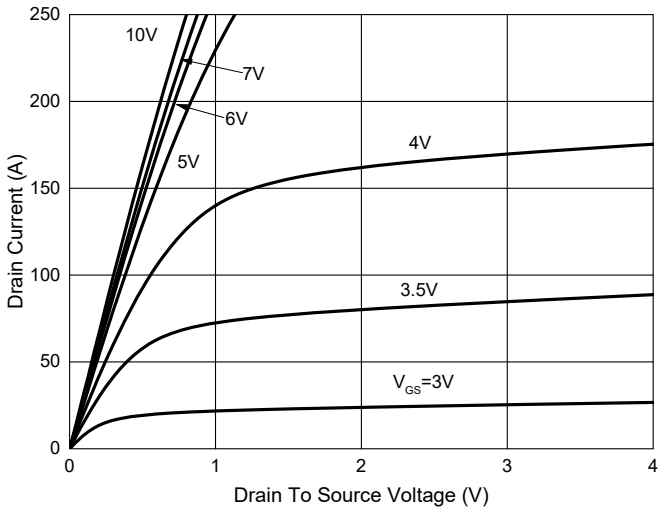


Fig. 2 - Transfer Characteristics

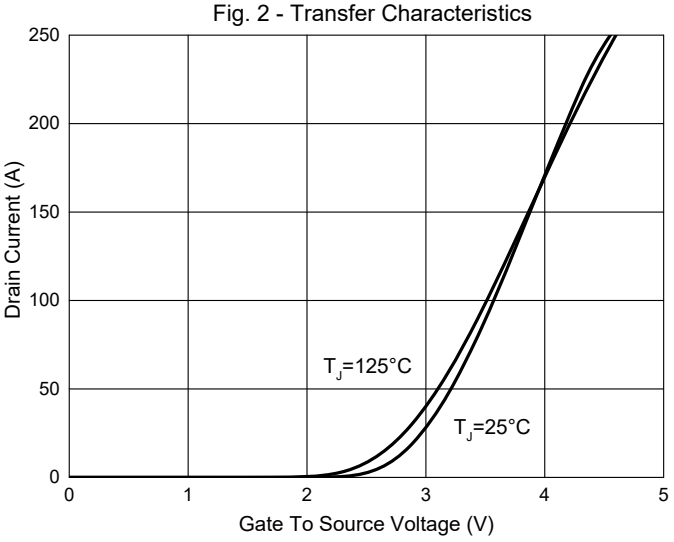


Fig. 3 - $R_{DS(ON)}$—I_D

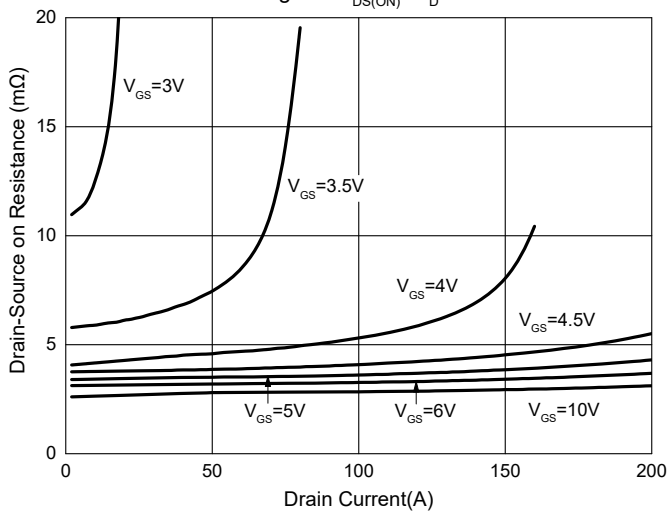


Fig. 4 - Drain-Source on Resistance

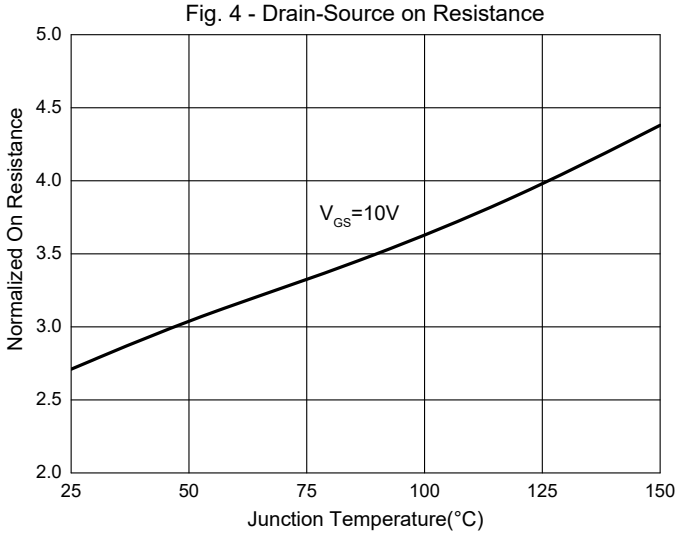


Fig. 5 - Capacitance Characteristics

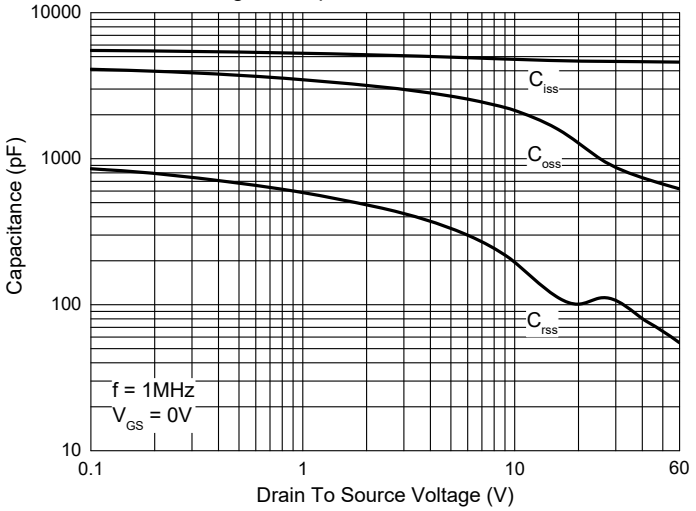
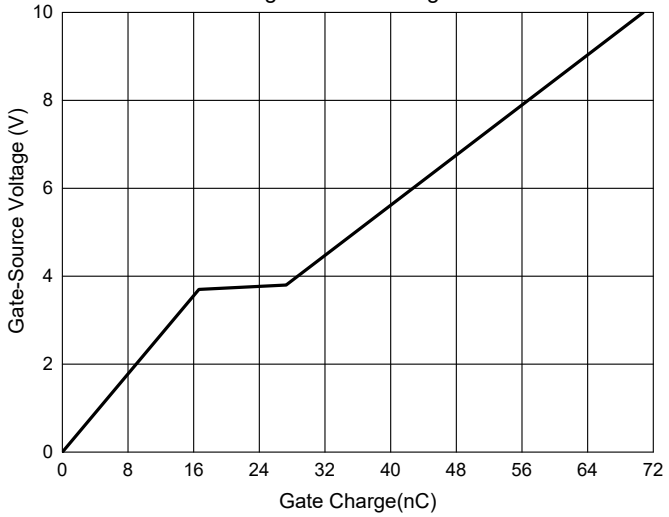


Fig. 6 - Gate Charge



Curve Characteristics

Fig. 7 - Safe Operation Area

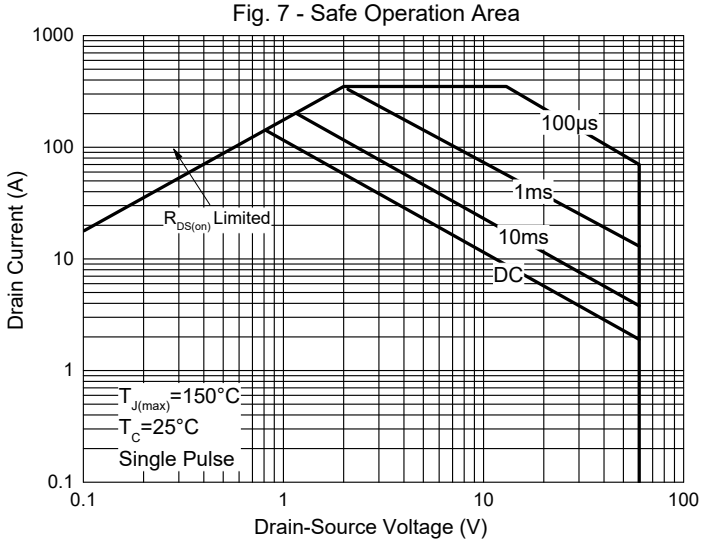
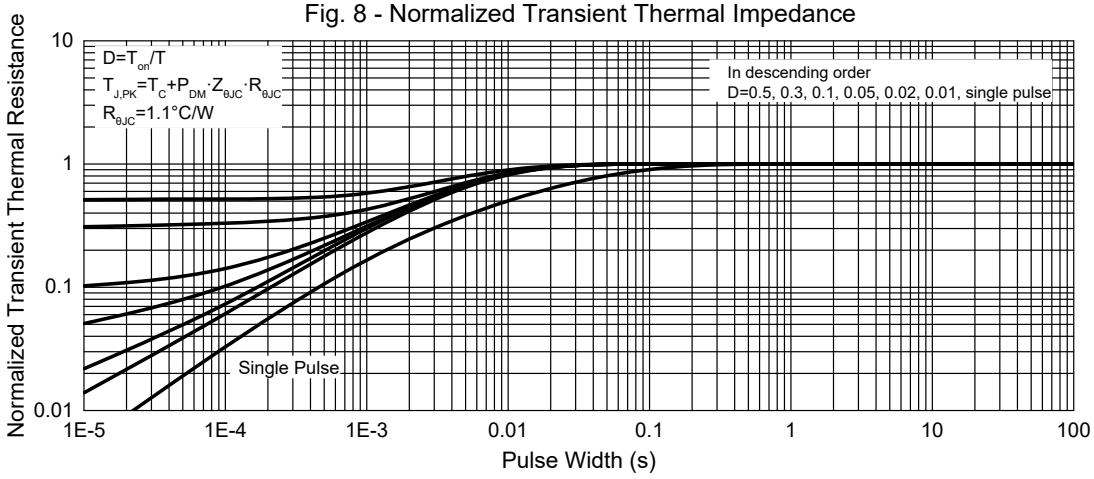


Fig. 8 - Normalized Transient Thermal Impedance



Ordering Information

Device	Packing
Part Number-TP	Tape&Reel: 5Kpcs/Reel